

Excellent Integrated System Limited

Stocking Distributor

Click to view price, real time Inventory, Delivery & Lifecycle Information:

[Vishay/Siliconix](#)
[SI4322DY-T1-E3](#)

For any questions, you can email us directly:

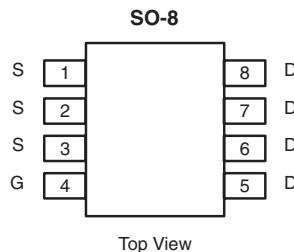
sales@integrated-circuit.com



N-Channel 30-V (D-S) MOSFET with Schottky Diode

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^a	Q_g (Typ.)
30	0.0085 at $V_{GS} = 10$ V	18	11.7 nC
	0.0125 at $V_{GS} = 4.5$ V	15	

SCHOTTKY AND BODY DIODE PRODUCT SUMMARY		
V_{DS} (V)	V_{SD} (V) Diode Forward Voltage	I_S (A)
30	0.4 at 2 A	5 ^a



FEATURES

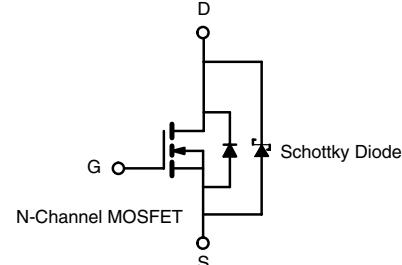
- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET® Power MOSFET
- 100 % R_g Tested



RoHS
COMPLIANT
HALOGEN
FREE
Available

APPLICATIONS

- Synchronous Buck-Low Side
 - Notebook
 - Server
 - Workstation
- Synchronous Rectifier-POL



Ordering Information: Si4322DY-T1-E3 (Lead (Pb)-free)
 Si4322DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 150$ °C)	$T_C = 25$ °C	18	
	$T_C = 70$ °C	15	
	$T_A = 25$ °C	14 ^{b, c}	
	$T_A = 70$ °C	11 ^{b, c}	
Pulsed Drain Current	I_{DM}	50	
Continuous Source-Drain Diode Current	$T_C = 25$ °C	5	
	$T_A = 25$ °C	2.8 ^{b, c}	
Maximum Power Dissipation	$T_C = 25$ °C	5.4	
	$T_C = 70$ °C	3.4	
	$T_A = 25$ °C	3.1 ^{b, c}	
	$T_A = 70$ °C	2.0 ^{b, c}	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typ.	Max.	Unit	
Maximum Junction-to-Ambient ^{b, d}	R_{thJA}	34	40	°C/W	
Maximum Junction-to-Foot (Drain)	R_{thJF}	17	23		

Notes:

- a. Based on $T_C = 25$ °C.
- b. Surface Mounted on 1" x 1" FR4 board.
- c. $t = 10$ s.
- d. Maximum under Steady State conditions is 85 °C/W.

Si4322DY

Vishay Siliconix



SPECIFICATIONS $T_J = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$	30			V
Gate-Source Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}$, $I_D = 250 \mu\text{A}$	1.5		3.0	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}$, $V_{GS} = \pm 20 \text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30 \text{ V}$, $V_{GS} = 0 \text{ V}$		0.18	1	mA
		$V_{DS} = 30 \text{ V}$, $V_{GS} = 0 \text{ V}$, $T_J = 100^\circ\text{C}$		22	100	
On -State Drain Current ^a	$I_{D(\text{on})}$	$V_{DS} \geq 5 \text{ V}$, $V_{GS} = 10 \text{ V}$	30			A
Drain-Source On-State Resistance ^a	$R_{DS(\text{on})}$	$V_{GS} = 10 \text{ V}$, $I_D = 15 \text{ A}$		0.007	0.0085	Ω
		$V_{GS} = 4.5 \text{ V}$, $I_D = 12 \text{ A}$		0.0095	0.012	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15 \text{ V}$, $I_D = 15 \text{ A}$		56		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = 15 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 1 \text{ MHz}$		1640		pF
Output Capacitance	C_{oss}			380		
Reverse Transfer Capacitance	C_{rss}			118		
Total Gate Charge	Q_g	$V_{DS} = 15 \text{ V}$, $V_{GS} = 10 \text{ V}$, $I_D = 15 \text{ A}$		25.5	38	nC
				11.7	17.5	
Gate-Source Charge	Q_{gs}	$V_{DS} = 15 \text{ V}$, $V_{GS} = 4.5 \text{ V}$, $I_D = 15 \text{ A}$		5.1		
Gate-Drain Charge	Q_{gd}			3.6		
Gate Resistance	R_g	$f = 1 \text{ MHz}$		2.3	3.5	Ω
Turn-On Delay Time	$t_{d(\text{on})}$	$V_{DD} = 15 \text{ V}$, $R_L = 3 \Omega$ $I_D \geq 5 \text{ A}$, $V_{GEN} = 4.5 \text{ V}$, $R_G = 1 \Omega$		24	36	ns
Rise Time	t_r			84	126	
Turn-Off Delay Time	$t_{d(\text{off})}$			36	54	
Fall Time	t_f			17	26	
Turn-On Delay Time	$t_{d(\text{on})}$			12	18	
Rise Time	t_r			36	54	
Turn-Off Delay Time	$t_{d(\text{off})}$	$V_{DD} = 15 \text{ V}$, $R_L = 3 \Omega$ $I_D \geq 5 \text{ A}$, $V_{GEN} = 10 \text{ V}$, $R_G = 1 \Omega$		36	54	ns
Fall Time	t_f			7	11	
Drain-Source Body Diode and Schottky Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25^\circ\text{C}$			5	A
Pulse Diode Forward Current ^a	I_{SM}				50	
Body Diode Voltage	V_{SD}	$I_S = 2 \text{ A}$		0.35	0.4	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 4 \text{ A}$, $dl/dt = 100 \text{ A}/\mu\text{s}$, $T_J = 25^\circ\text{C}$		26	40	ns
Body Diode Reverse Recovery Charge	Q_{rr}			16	25	nC
Reverse Recovery Fall Time	t_a			12.5		ns
Reverse Recovery Rise Time	t_b			13.5		

Notes:

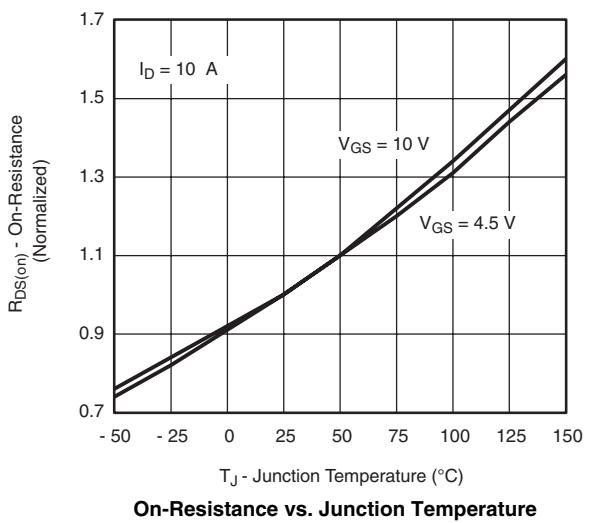
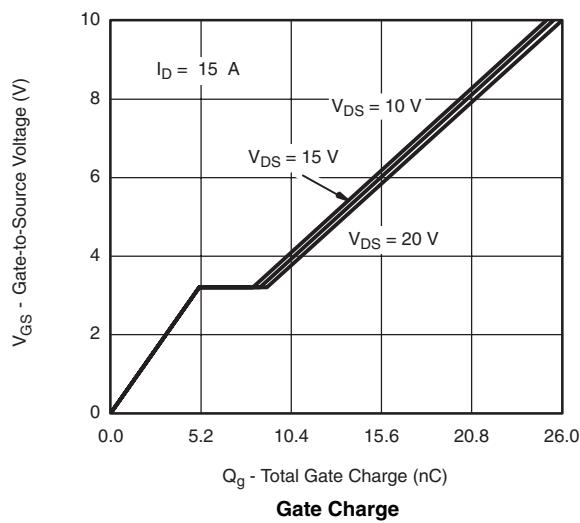
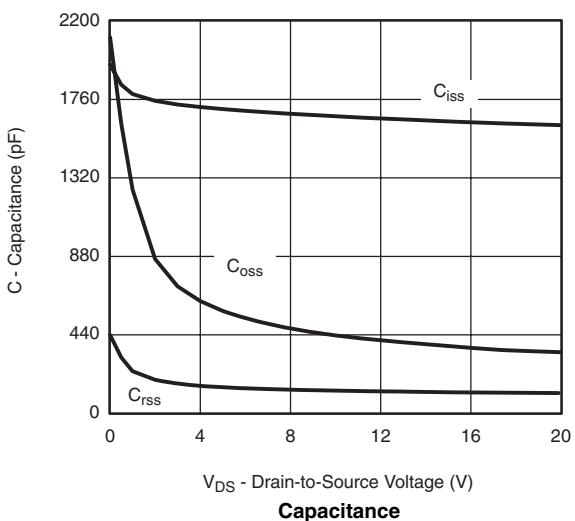
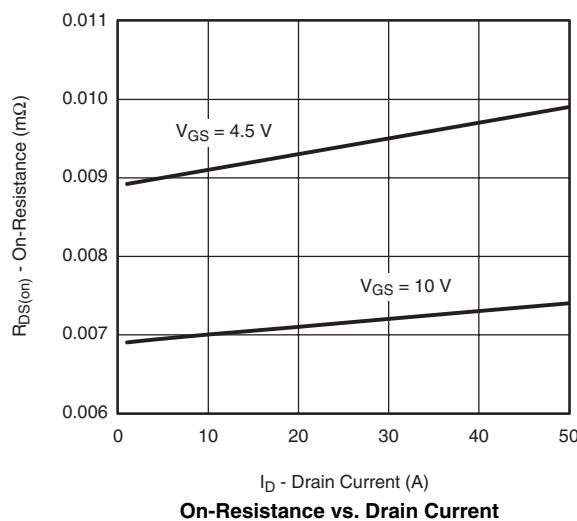
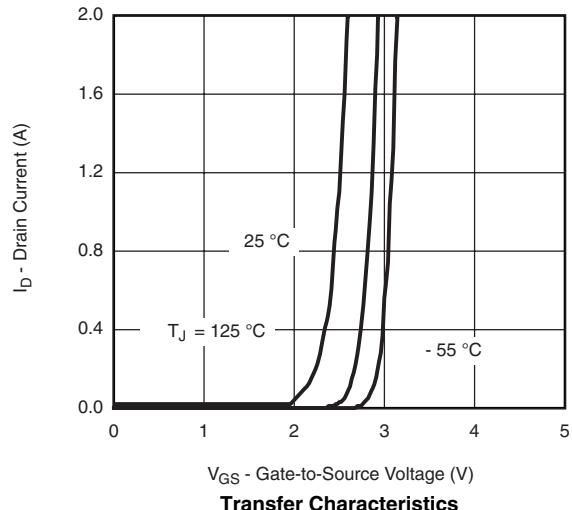
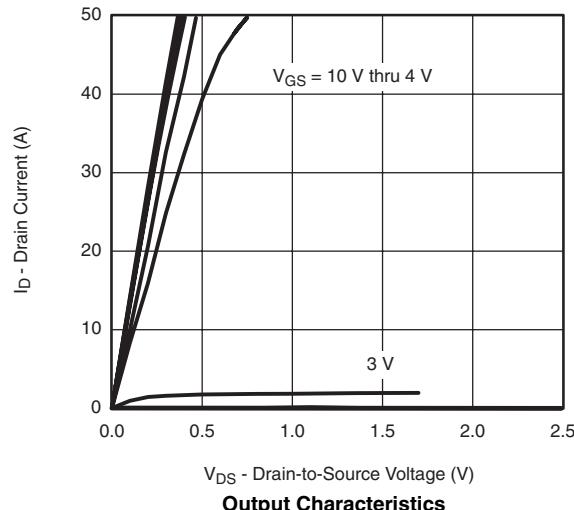
a. Pulse test; pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

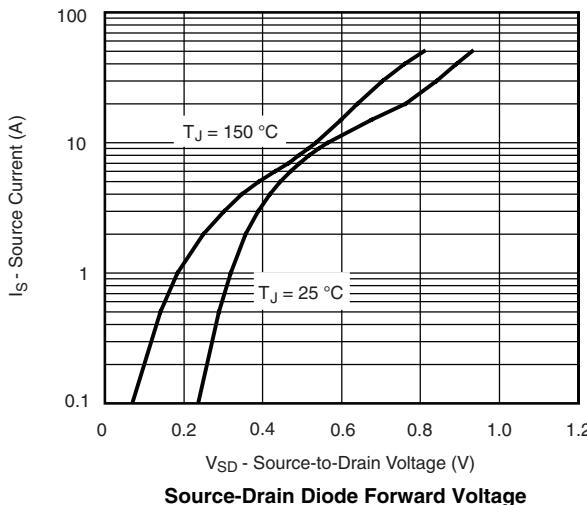


Si4322DY

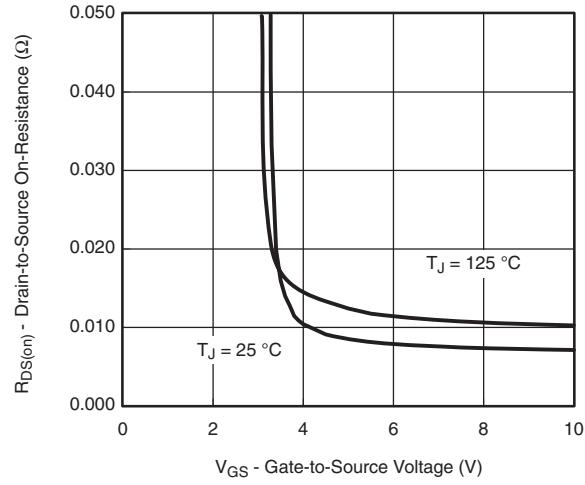
Vishay Siliconix



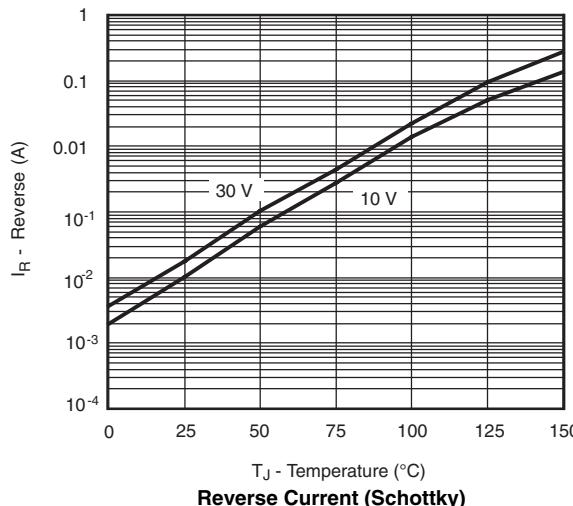
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



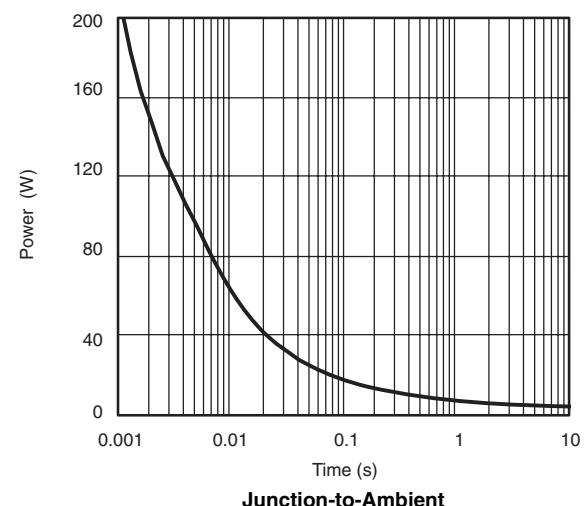
Source-Drain Diode Forward Voltage



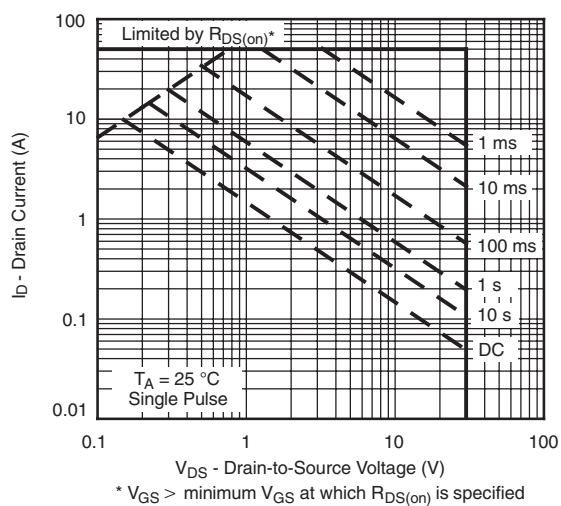
On-Resistance vs. Gate-to-Source Voltage



Reverse Current (Schottky)



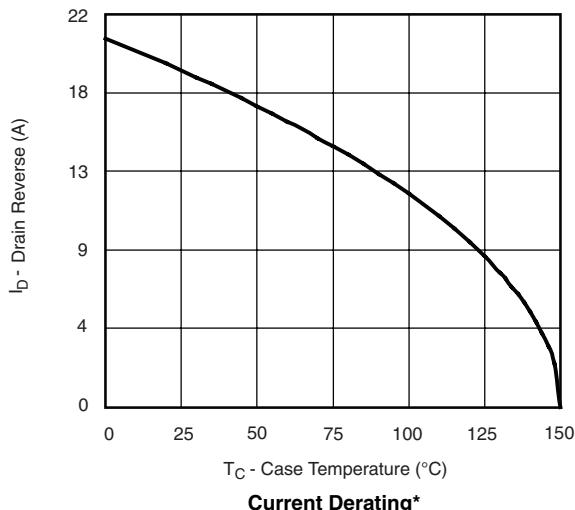
Junction-to-Ambient



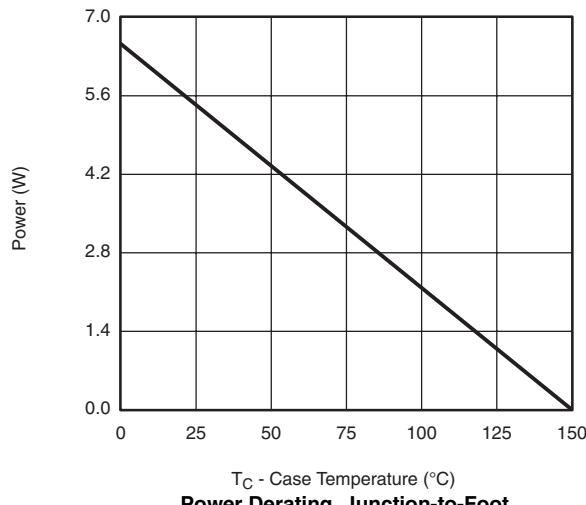
Safe Operating Area



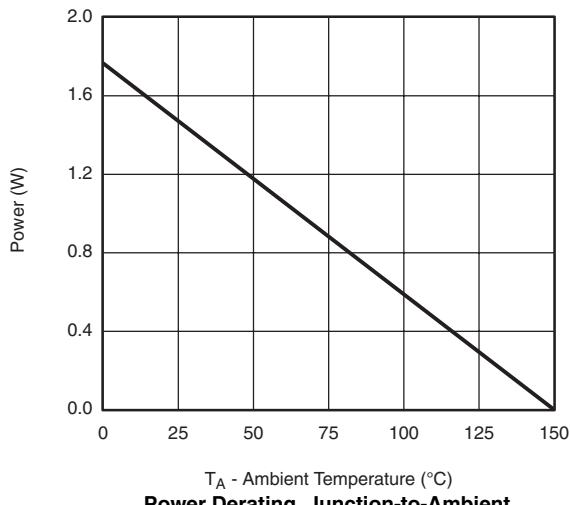
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Current Derating*



Power Derating, Junction-to-Foot



Power Derating, Junction-to-Ambient

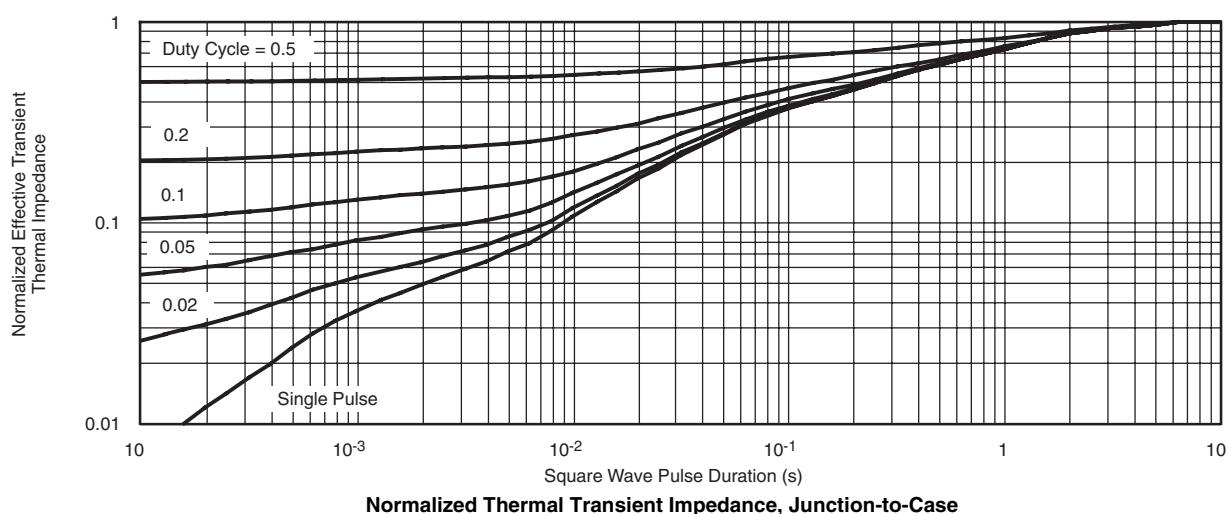
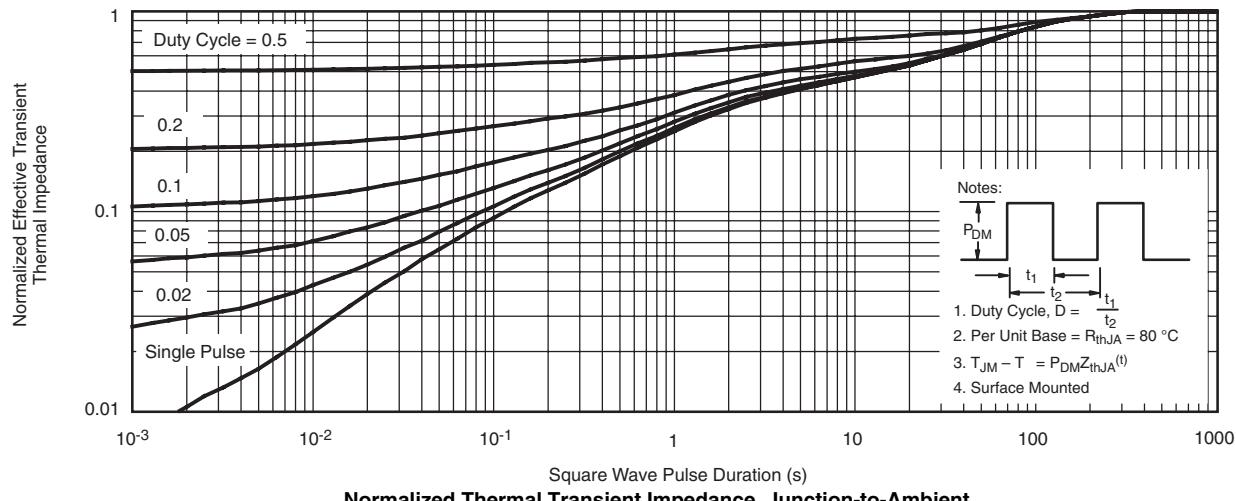
* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

Si4322DY

Vishay Siliconix



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?73860.



Legal Disclaimer Notice

Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.